

B

The ZM060N06B combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

A

Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

nd Synchronous Rectifier

Product Summary

 $V_{DS}=60V$
 $R_{DS(ON)} = 6m\Omega$
 $I_D=80A$


TO-263

Part NO.	ZM060N06B
Marking	ZM060N06
Packing Information	Bulk Tube
Basic ordering unit (pcs)	500

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_D@T_C=25$	80	A
	$I_D@T_C=75$	60.8	A
	$I_D@T_C=100$	50.4	A
Pulsed Drain Current	I_{DM}	190	A
Total Power Dissipation	$P_D@T_C=25$	120	W
Total Power Dissipation	$P_D@T_A=25$	5	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	210	mJ



Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

Fig.4 Typical output Characteristics

Fig.7 On-Resistance VS Gate Source Voltage

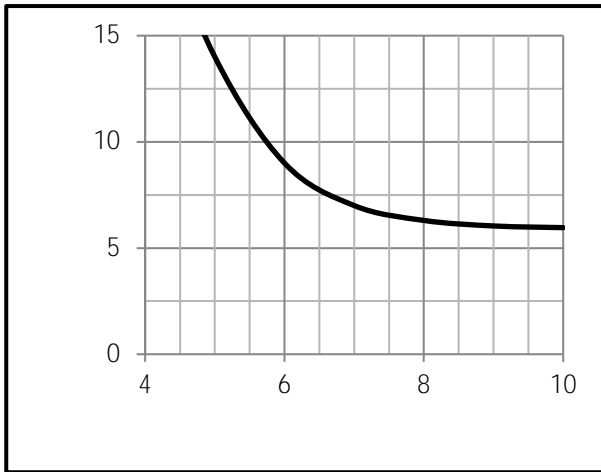


Fig.8 On-Resistance V.S Junction Temperature

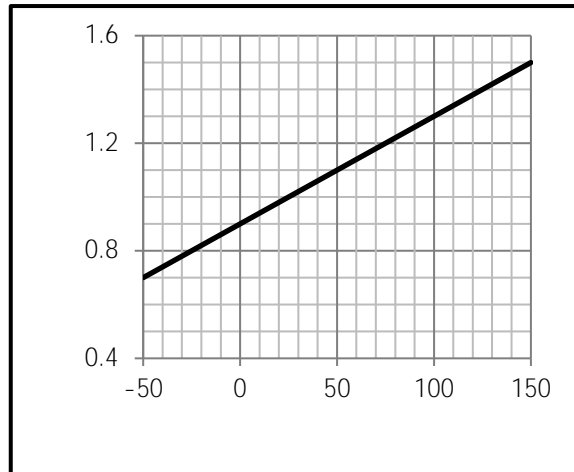


Fig.9 Switching Time Measurement Circuit

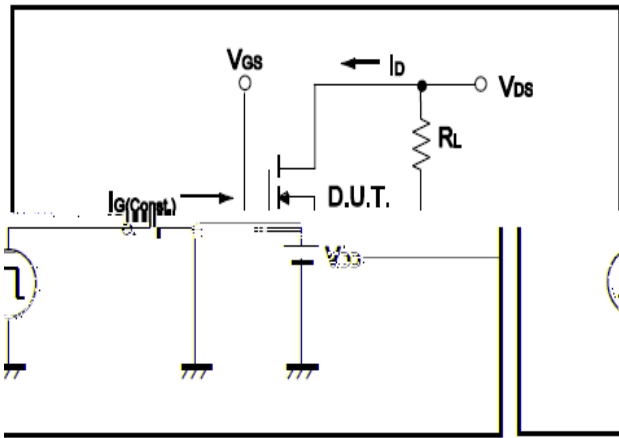


Fig.10 Gate Charge Waveform

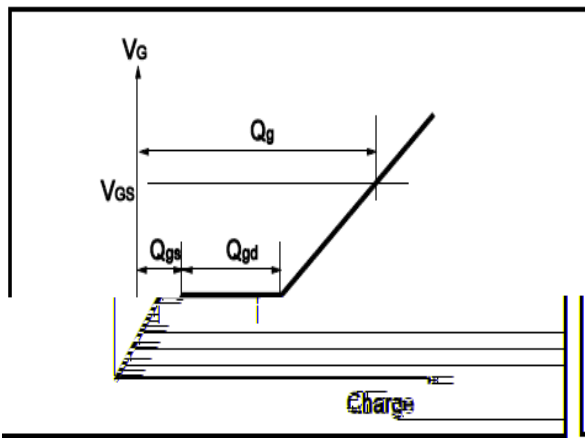


Fig.11 Switching Time Measurement Circuit

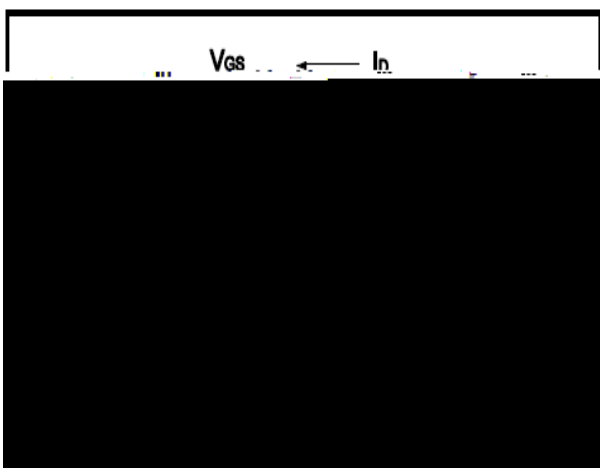


Fig.12 Gate Charge Waveform

